L	Hits	Search Text	DB	Time stamp
Number				
, 1	60616	template	USPAT;	2002/06/21
			EPO; JPO;	09:25
1			DERWENT	
2	697	nanoparticle nanomer	USFAT;	2000/06/21
	ļ		EPO; JPO;	09:25
			DEFWENT	Ī
3	316161	deposition	USFAT;	72002/06/21
			EPO; JPO;	109:35
			DEFWENT	
4	119822	427/\$.ccls.	: USFAT;	.00:/06/21
			EPO; JPO;	19:26
5	20724	205/4	DEPWENT	
5	32/34	205/\$.ccls.	USFAT;	2002/06/21
1	 		EPO; JPO;	09:26
. 6	1106446		DEPWENT	į :
. 0	1106449	semiconductor	USFAT;	12002/06/21
			EPO; JPO;	09:16
7	122626		DEFWENT	
. /	132636	metal adj (oxide chalcogenide oxide	USPAT;	1002/06/21
		sulfide)	EPO; JPO;	09:27
: 8	51000		DEFWENT	
0	51009		USFAT;	2002/06/21
		nitride)	EPO; JPO;	09:27
. 9	222		DEPWENT	
9	322	metal adj (phosphide antimonide)	USPAT;	2002/06/21
1			EPO; JPO;	19:27
10	178597	(m-4-1 - 3- /	DEPWENT	1
110	1/859/	(metal adj (oxide chalcogenide oxide	USPAT;	1002/06/21
1 1		sulfide)) (metal adj (selenide telluride	EPC; JPO;	÷9:27
		alloy nitride)) (metal adj (phosphide	DERWENT	!
111	1238387	antimonide))	1	
++	1230307	((metal adj (oxide chalcogenide oxide	USPAT;	1002/06/21
Î A	T	sulfide)) (metal adj (selenide telluride	EPO; JPO;	09:28
	1	alloy nitride)) (metal adj (phosphide	DEFWENT	1
12	7 !	antimonide))) semiconductor		
12	,	(((metal adj (oxide chalcogenide oxide	USFAT;	2002/06/21
		sulfide)) (metal adj (selenide telluride	i ·	09:30
1		alloy nitride)) (metal adj (phosphide	DEFWENT	
		antimonide))) semiconductor) and		
1 1		deposition and (nanoparticle nanomer) and template		
14		(((metal adj (oxide chalcogenide oxide	110	
1 .	2	sulfide)) (metal adj (selenide telluride	USFAT;	2002/06/21
	!	allow mitride) / /metal add /stende telluride	EPO; JPO;	09:31
		alloy nitride)) (metal adj (phosphide	DERWENT	į.
1	1	antimonide))) semiconductor) and deposition and (nanoparticle nanomer) and	!	
	:	205/\$.ccls.		1
13	22	(((metal adj (oxide chalcogenide oxide		
	22 1	sulfide) /motal add (calculate that is	USPAT;	2002/06/21
		<pre>sulfide)) (metal adj (selenide telluride alloy nitride)) (metal adj (phosphide</pre>	EPO; JPO;	09:31
1	j	antimonide)) ) semiconductor) and	DERWENT	
1	}	deposition and (nanoparticle nanomer) and		i i
		427/\$.ccls.	J	
		1677 7 1 0013 .	l	